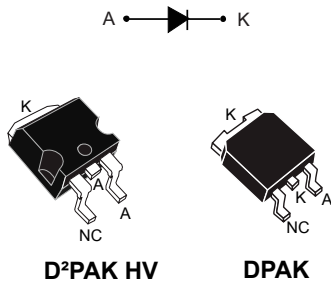


## Automotive 650 V, 8 A high surge silicon carbide power Schottky diode

### Features



- AEC-Q101 qualified 
- No reverse recovery charge in application current range
- Switching behavior independent of temperature
- Recommended to PFC applications
- PPAP capable
- $V_{RRM}$  guaranteed from  $-40$  to  $175$  °C
- D²PAK HV creepage distance (anode to cathode) = 5.38 mm min. (with top coating)
- **ECOPACK2** compliant component

### Applications

- On board battery charger (OBC)

### Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, the SiC diode will boost performance in hard switching conditions.

#### Product label



#### Product status

STPSC8H065-Y

#### Product summary

| Symbol        | Value    |
|---------------|----------|
| $I_{F(AV)}$   | 8 A      |
| $V_{RRM}$     | 650 V    |
| $T_{J(max.)}$ | $175$ °C |

# 1 Characteristics

**Table 1. Absolute ratings (limiting values at 25 °C unless otherwise specified)**

| Symbol              | Parameter                            |                                                                           | Value       | Unit |
|---------------------|--------------------------------------|---------------------------------------------------------------------------|-------------|------|
| V <sub>RRM</sub>    | Repetitive peak reverse voltage      | T <sub>j</sub> = -40 °C to + 175 °C                                       | 650         | V    |
| I <sub>F(RMS)</sub> | Forward rms current                  |                                                                           | 22          | A    |
| I <sub>F(AV)</sub>  | Average forward current              | T <sub>c</sub> = 145 °C <sup>(1)</sup> , DC                               | 8           | A    |
| I <sub>FSM</sub>    | Surge non repetitive forward current | t <sub>p</sub> = 10 ms sinusoidal, T <sub>c</sub> = 25 °C                 | 75          | A    |
|                     |                                      | t <sub>p</sub> = 10 ms sinusoidal, T <sub>c</sub> = 125 °C                | 69          |      |
|                     |                                      | t <sub>p</sub> = 10 μs square, T <sub>c</sub> = 25 °C                     | 420         |      |
| I <sub>FRM</sub>    | Repetitive peak forward current      | T <sub>c</sub> = 145 °C <sup>(1)</sup> , T <sub>j</sub> = 175 °C, δ = 0.1 | 33          | A    |
| T <sub>stg</sub>    | Storage temperature range            |                                                                           | -55 to +175 | °C   |
| T <sub>j</sub>      | Operating junction temperature range |                                                                           | -40 to +175 | °C   |

1. Value based on R<sub>th(j-c)</sub> max.

**Table 2. Thermal resistance parameters**

| Symbol               | Parameter        | Typ. value | Max. value | Unit |
|----------------------|------------------|------------|------------|------|
| R <sub>th(j-c)</sub> | Junction to case | 1.3        | 1.6        | °C/W |

**Table 3. Static electrical characteristics**

| Symbol                        | Parameter               | Test conditions         |                                   | Min. | Typ. | Max. | Unit |
|-------------------------------|-------------------------|-------------------------|-----------------------------------|------|------|------|------|
| I <sub>R</sub> <sup>(1)</sup> | Reverse leakage current | T <sub>j</sub> = 25 °C  | V <sub>R</sub> = V <sub>RRM</sub> | -    | 7    | 80   | μA   |
|                               |                         | T <sub>j</sub> = 150 °C |                                   | -    | 65   | 335  |      |
| V <sub>F</sub> <sup>(2)</sup> | Forward voltage drop    | T <sub>j</sub> = 25 °C  | I <sub>F</sub> = 8 A              | -    | 1.45 | 1.65 | V    |
|                               |                         | T <sub>j</sub> = 150 °C |                                   | -    | 1.7  | 2.05 |      |

1. t<sub>p</sub> = 10 ms, δ < 2%

2. t<sub>p</sub> = 500 μs, δ < 2%

To evaluate the conduction losses, use the following equation:

$$P = 0.972 \times I_{F(AV)} + 0.135 \times I_{F(RMS)}^2$$

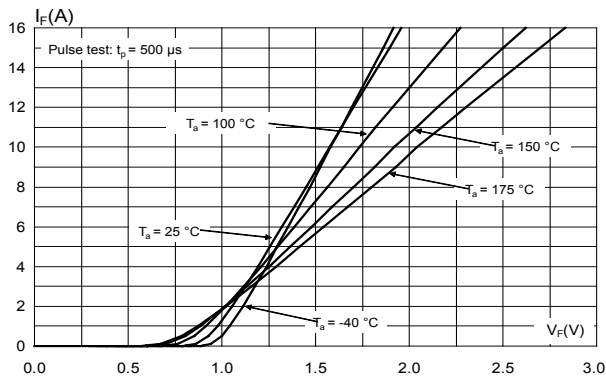
**Table 4. Dynamic electrical characteristics**

| Symbol                         | Parameter               | Test conditions                                           | Typ. | Unit |
|--------------------------------|-------------------------|-----------------------------------------------------------|------|------|
| Q <sub>cj</sub> <sup>(1)</sup> | Total capacitive charge | V <sub>R</sub> = 400 V                                    | 23.5 | nC   |
| C <sub>j</sub>                 | Total capacitance       | V <sub>R</sub> = 0 V, T <sub>c</sub> = 25 °C, F = 1 MHz   | 414  | pF   |
|                                |                         | V <sub>R</sub> = 400 V, T <sub>c</sub> = 25 °C, F = 1 MHz | 38   |      |

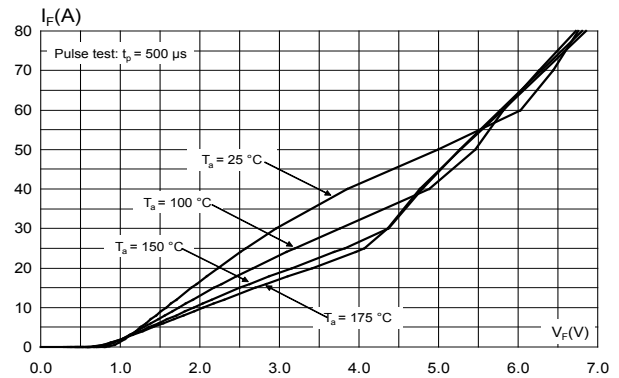
1. Most accurate value for the capacitive charge:  $Q_{cj}(V_R) = \int_0^{V_R} C_j(V) dV$

## 1.1 Characteristics (curves)

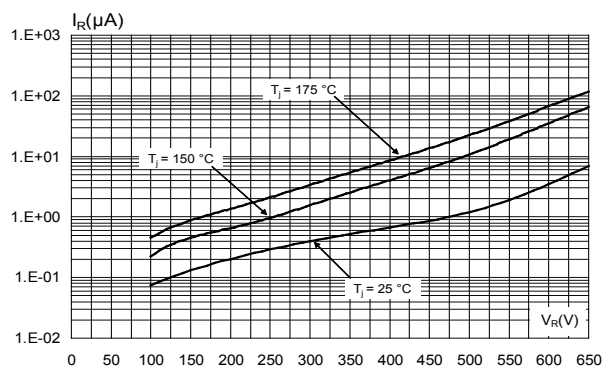
**Figure 1. Forward voltage drop versus forward current (typical values, low level)**



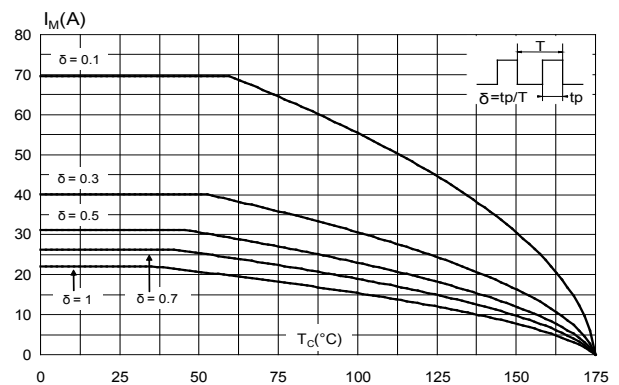
**Figure 2. Forward voltage drop versus forward current (typical values, high level)**



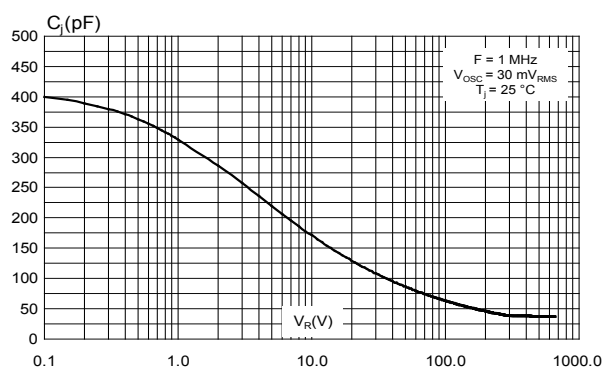
**Figure 3. Reverse leakage current versus reverse voltage applied (typical values)**



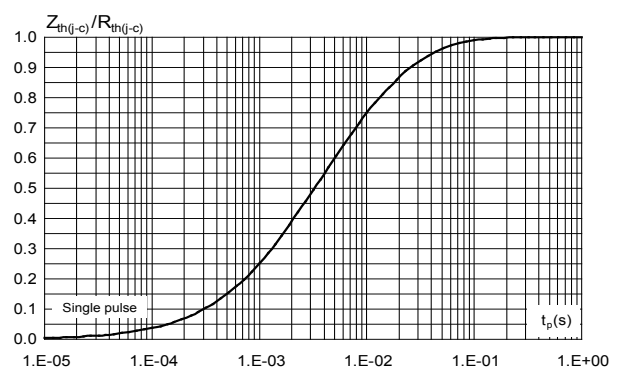
**Figure 4. Peak forward current versus case temperature**



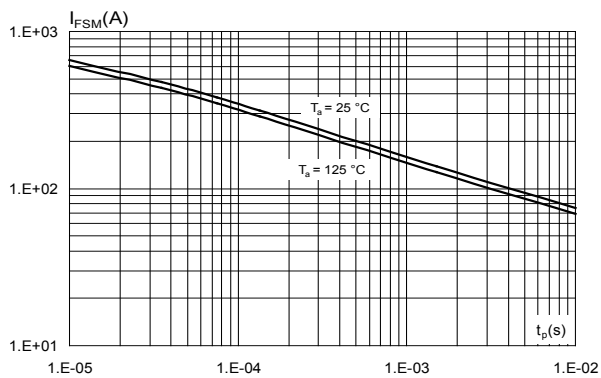
**Figure 5. Junction capacitance versus reverse voltage applied (typical values)**



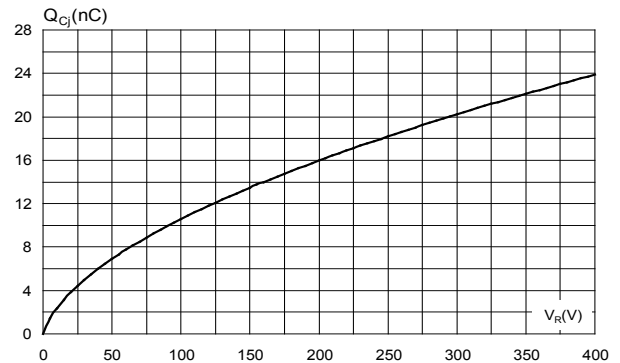
**Figure 6. Relative variation of thermal impedance junction to case versus pulse duration**



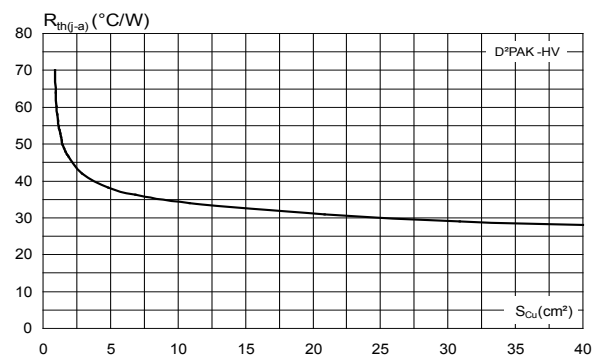
**Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)**



**Figure 8. Total capacitive charges versus reverse voltage applied (typical values)**



**Figure 9. Thermal resistance junction to ambient versus copper surface under tab (typical values, epoxy printed board FR4,  $e_{Cu} = 35\text{ }\mu\text{m}$ ) (D<sup>2</sup>PAK-HV)**



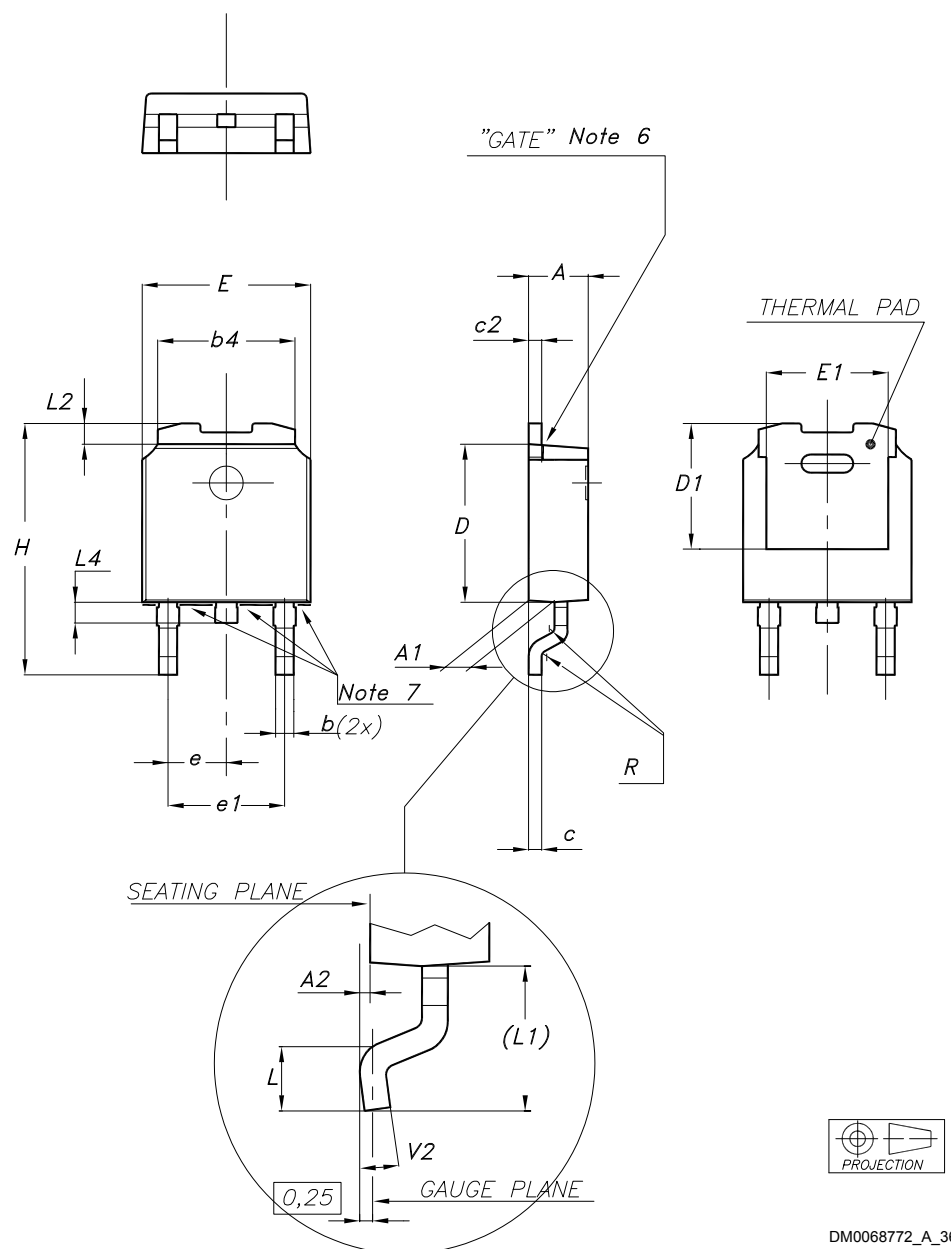
## 2 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 2.1 DPAK package information

- Epoxy meets UL94, V0

**Figure 10. DPAK package outline**



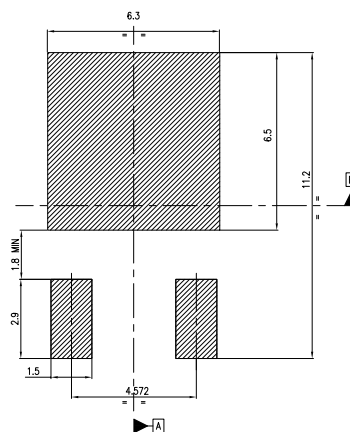
DM0068772\_A\_36

**Note:** This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

**Table 5. DPAK mechanical data**

| Dim. | Dimensions  |       |       |                       |       |       |
|------|-------------|-------|-------|-----------------------|-------|-------|
|      | Millimeters |       |       | Inches <sup>(1)</sup> |       |       |
|      | Min.        | Typ.  | Max.  | Min.                  | Typ.  | Max.  |
| A    | 2.20        |       | 2.40  | 0.087                 |       | 0.094 |
| A1   | 0.90        |       | 1.10  | 0.035                 |       | 0.043 |
| A2   | 0.03        |       | 0.23  | 0.001                 |       | 0.009 |
| b    | 0.64        |       | 0.90  | 0.025                 |       | 0.035 |
| b4   | 5.20        |       | 5.40  | 0.205                 |       | 0.213 |
| c    | 0.45        |       | 0.60  | 0.018                 |       | 0.024 |
| c2   | 0.48        |       | 0.60  | 0.019                 |       | 0.024 |
| D    | 6.00        |       | 6.20  | 0.236                 |       | 0.244 |
| D1   | 4.95        | 5.10  | 5.25  | 0.195                 | 0.201 | 0.207 |
| E    | 6.40        |       | 6.60  | 0.252                 |       | 0.260 |
| E1   | 4.60        | 4.70  | 4.80  | 0.181                 | 0.185 | 0.189 |
| e    | 2.159       | 2.286 | 2.413 | 0.085                 | 0.090 | 0.095 |
| e1   | 4.445       | 4.572 | 4.699 | 0.175                 | 0.180 | 0.185 |
| H    | 9.35        |       | 10.10 | 0.368                 |       | 0.398 |
| L    | 1.00        |       | 1.50  | 0.039                 |       | 0.059 |
| (L1) | 2.60        | 2.80  | 3.00  | 0.102                 | 0.110 | 0.118 |
| L2   | 0.65        | 0.80  | 0.95  | 0.026                 | 0.031 | 0.037 |
| L4   | 0.60        |       | 1.00  | 0.024                 |       | 0.039 |
| R    |             | 0.20  |       |                       | 0.008 |       |
| V2   | 0°          |       | 8°    | 0°                    |       | 8°    |

1. Inches dimensions given for reference only

**Figure 11. DPAK recommended footprint (dimensions are in mm)**


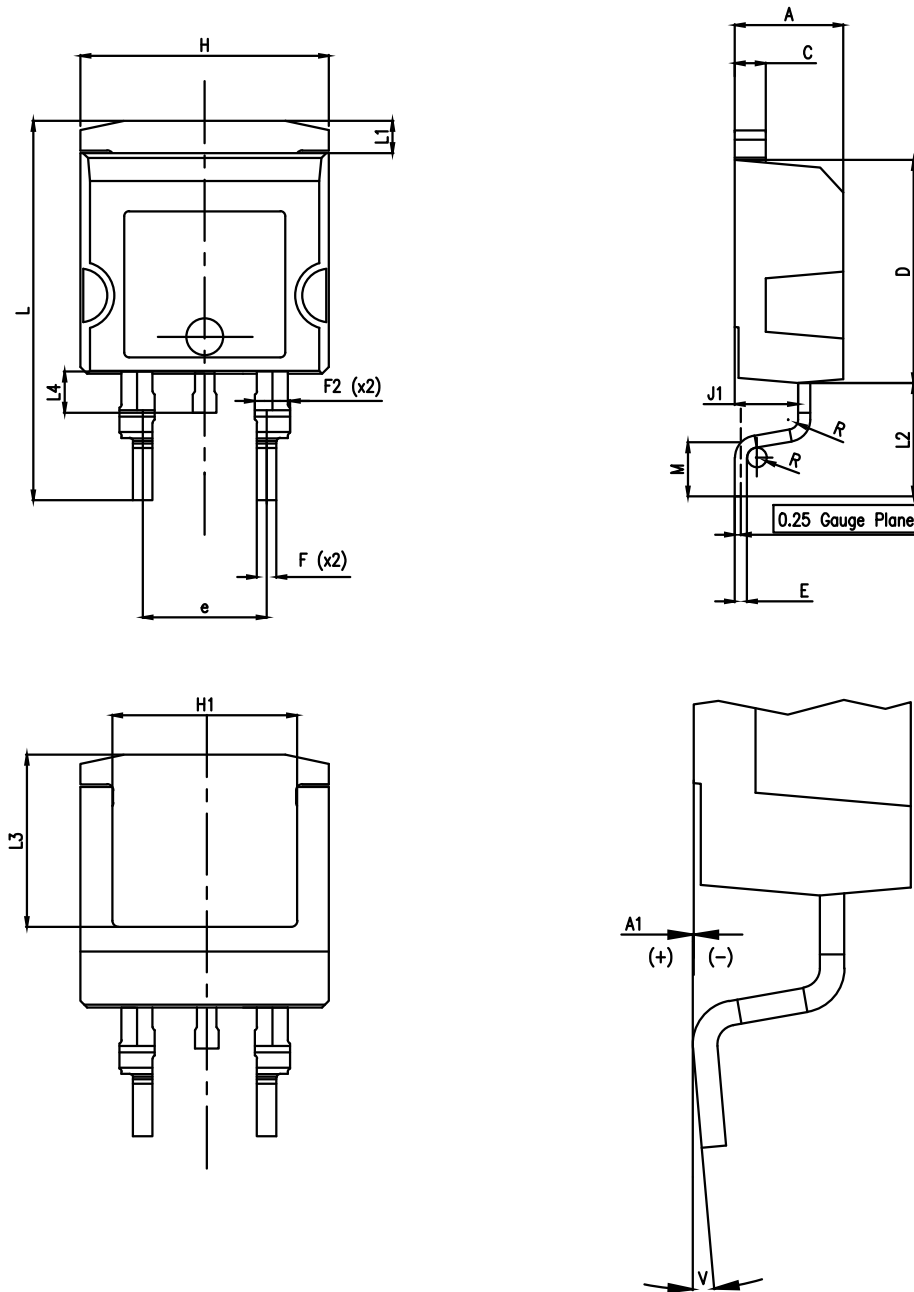
Notes:  
 1) This footprint is able to ensure insulation up to 630 Vrms (according to CEI IEC 664-1)  
 2) The device must be positioned within  $\pm 0.05$  [A] [B]

FP\_0068772\_E

**Note:** For package and tape orientation, reel and inner box dimensions and tape outline see [TN1173](#).

## 2.2 D<sup>2</sup>PAK HV package information

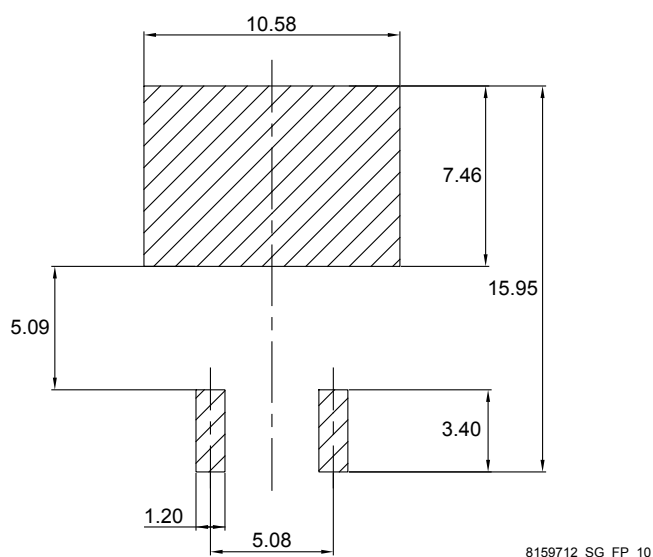
Figure 12. D<sup>2</sup>PAK high voltage package outline



8159712\_SG\_10

**Table 6. D<sup>2</sup>PAK high voltage package mechanical data**

| Ref. | Dimensions |      |       |
|------|------------|------|-------|
|      | Min.       | Typ. | Max.  |
| A    | 4.30       | -    | 4.70  |
| A1   | -0.05      | -    | 0.08  |
| C    | 1.17       | -    | 1.37  |
| D    | 8.95       | -    | 9.35  |
| e    | 4.98       | -    | 5.18  |
| E    | 0.50       | -    | 0.90  |
| F    | 0.78       | -    | 0.85  |
| F2   | 1.14       | -    | 1.70  |
| H    | 10.00      | -    | 10.40 |
| H1   | 7.40       | -    | 7.80  |
| J1   | 2.49       | -    | 2.69  |
| L    | 15.30      | -    | 15.80 |
| L1   | 1.27       | -    | 1.40  |
| L2   | 4.93       | -    | 5.23  |
| L3   | 6.85       | -    | 7.25  |
| L4   | 1.5        | -    | 1.7   |
| M    | 2.6        | -    | 2.9   |
| R    | 0.20       | -    | 0.60  |
| V    | 0°         | -    | 8°    |

**Figure 13. D<sup>2</sup>PAK high voltage footprint in mm**




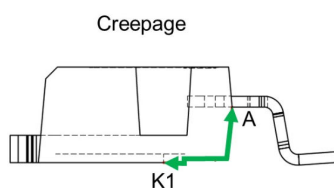
## 2.2.1 Creepage distance between anode and cathode

**Table 7. Creepage distance between anode and cathode**

| Symbol             | Parameter                                                        |                       | Value | Unit |
|--------------------|------------------------------------------------------------------|-----------------------|-------|------|
| Cd <sub>A-K1</sub> | Minimum creepage distance between A and K1 (with top coating)    | D <sup>2</sup> PAK HV | 5.38  | mm   |
| Cd <sub>A-K2</sub> | Minimum creepage distance between A and K2 (without top coating) |                       | 3.48  |      |

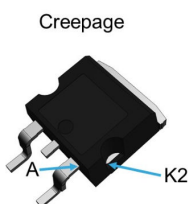
*Note:* D<sup>2</sup>PAK HV creepage distance (anode to cathode) = 5.38 mm min. (refer to IEC 60664-1)

**Figure 14. Creepage with top coating**



Minimum distance between A & K1 = 5.38 mm (with top coating)

**Figure 15. Creepage without top coating**



Minimum distance between A & K2 = 3.48 mm (without top coating)

### 3 Ordering Information

**Table 8. Ordering information**

| Order code       | Marking     | Package               | Weight | Base qty. | Delivery mode |
|------------------|-------------|-----------------------|--------|-----------|---------------|
| STPSC8H065BY-TR  | PSC8H 065Y  | DPAK                  | 0.32 g | 2500      | Tape and reel |
| STPSC8H065G2Y-TR | PSC8H065G2Y | D <sup>2</sup> PAK HV | 1.48 g | 1000      | Tape and reel |

## Revision history

**Table 9. Document revision history**

| Date        | Version | Changes                                                                                                                                                          |
|-------------|---------|------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 08-Mar-2018 | 1       | Initial release.                                                                                                                                                 |
| 11-Sep-2018 | 2       | Added D <sup>2</sup> PAK HV package.                                                                                                                             |
| 06-Dec-2018 | 3       | Updated <a href="#">Section 2.2.1</a> : Creepage distance between anode and cathode.<br>Minor text changes to improve readability.<br>Updated title of document. |
| 08-Oct-2025 | 4       | Updated <a href="#">Section Features</a> , <a href="#">Table 6</a> , and <a href="#">Table 8</a> .                                                               |

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